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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application of  
Shunpei YAMAZAKI et al.

Serial No. 09/362,192

Filed: July 28, 1999

For: SEMICONDUCTOR DEVICE  
HAVING SEMICONDUCTOR CIRCUIT  
COMPRISING SEMICONDUCTOR  
ELEMENT, AND METHOD FOR  
MANUFACTURING THE SAME

) Art Unit: 2812

) Examiner: V. Simkovic

**CERTIFICATE OF MAILING**

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Washington, D.C. 20231, on 10/21/02

**AMENDMENT**

Honorable Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated May 14, 2002, please amend the above-  
identified application as follows:

**IN THE CLAIMS:**

Please cancel claims 51, 55, 59, 63 and 66 and amend claims 45, 49, 52, 56, 60  
and 64 as follows:

E 1  
· 45. (Amended) A method for manufacturing a semiconductor device  
comprising steps of:

providing a material for promoting crystallization to at least a part of a  
semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma to form a gate  
insulating film on said semiconductor film; and

crystallizing said semiconductor film after subjecting said semiconductor  
film to the oxygen plasma to obtain a crystalline semiconductor film.

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